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Substitute for Form 1449B/PTO		Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		Application Number	10/826,007
Date Submitted: July 10, 2006		Filing Date	04/16/2004
(use as many sheets as necessary)		First Named Inventor	Hongxing TANG
		Group Art Unit	2855
		Examiner Name	George P. Bonanto
		Attorney Docket Number	049411-0268
Sheet	1	of	3

U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
MN ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓	B1	2002/0175408	A1	MAJUMDAR et al.	11/28/2002	
	B2	2003/0203531	A1	SHCHUKIN et al.	10/30/2003	
	B3	2005/0109925	A1	EL RIFAI et al.	05/2005	
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	B6	3,034,345		MASON	05/15/1962	
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U.S. PATENT APPLICATION DOCUMENTS						
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FOREIGN PATENT DOCUMENTS								
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MN	B14	WO	2003/095616	A2	California Inst. of Tech.	11/20/2003		
MN	B15	WO	2003/095617	A2	California Inst. of Tech.	11/20/2003		
MN	B16	WO	2004/041998	A2	California Inst. of Tech.	05/21/2004		

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MN	B17	MELOSH et al., "Ultrahigh-Density Nanowire Lattices and Circuits," Science, April 4, 2003, vol. 300, pp. 112-115.	

Examiner Signature	/Max Noori/	Date Considered	07/27/2006
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	B30	PATRIDGE et al., "High-performance planar peizoresistive accelerometer," JMEMS, March 1, 2000, vol. 9, no. 1, pp. 58-66.	
	B31	CHUI et al., "Independent detection of vertical and lateral forces with a sidewall-implanted dual-axis piezoresistive cantilever," Appl. Phys. Lett., March 16, 1998, vol. 72, no. 11, pp. 1388-1390.	

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MN	B32	DEHE et al., "A piezoresistive GaAs pressure sensor with GaAs/AlGaAs membrane technology," J. Micromech. Microeng., 1995, vol. 5, pp. 139-142.	
	B33	HSU et al., "Piezoresistive response induced by piezoelectric charges in n-type GaAs mesa resistors for application in stress transducers," J. Appl. Phys. January 1, 1999, vol. 85, no. 1, pp. 333-340.	
	B34	TANG et al., "Two-dimensional electron-gas actuation and transduction for GaAs nanoelectromechanical systems," Appl. Phys. Lett. November 11, 2002, vol. 81, no. 20, pp. 3879-3881.	
	B35	KONCZEWICZ et al., "GaAlAs-Based Micromachined Accelerometer," Phys. Stat. Sol. B, 2001, vol. 223, pp. 593-596.	
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